

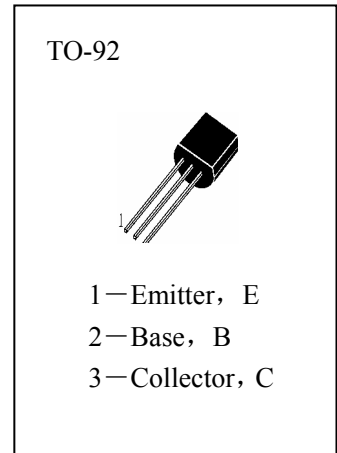


APPLICATIONS

General Purpose Amplifier.

ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

- T_{stg}—Storage Temperature..... -55~150°C
- T_j—Junction Temperature.....150°C
- P_C—Collector Dissipation.....625mW
- V_{CBO}—Collector-Base Voltage.....80V
- V_{CEO}—Collector-Emitter Voltage.....80V
- V_{EBO}—Emitter-Base Voltage.....4V
- I_C—Collector Current.....500mA



ELECTRICAL CHARACTERISTICS (Ta=25°C)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BV _{CEO}	Collector-Emitter Breakdown Voltage	80			V	I _C =1mA, I _B =0
BV _{EBO}	Emitter-Base Breakdown Voltage	4			V	I _E =100 μ A, I _C =0
H _{FE} (1)	DC Current Gain	50				V _{CE} =1V, I _C =10mA
H _{FE} (2)	DC Current Gain	50				V _{CE} =1V, I _C =100mA
V _{CE(sat)}	Collector- Emitter Saturation Voltage			0.25	V	I _C =100mA, I _B =10mA
V _{BE (on)}	Base-Emitter On Voltage			1.2	V	V _{CE} =1V, I _C =100mA
I _{CBO}	Collector Cut-off Current			100	nA	V _{CB} =80V, I _E =0
I _{CEO}	Collector Cut-off Current			100	nA	V _{CE} =60V, I _B =0
f _T	Current Gain-Bandwidth Product	100			MHz	V _{CE} =20V, I _C =10mA, f=100MHz